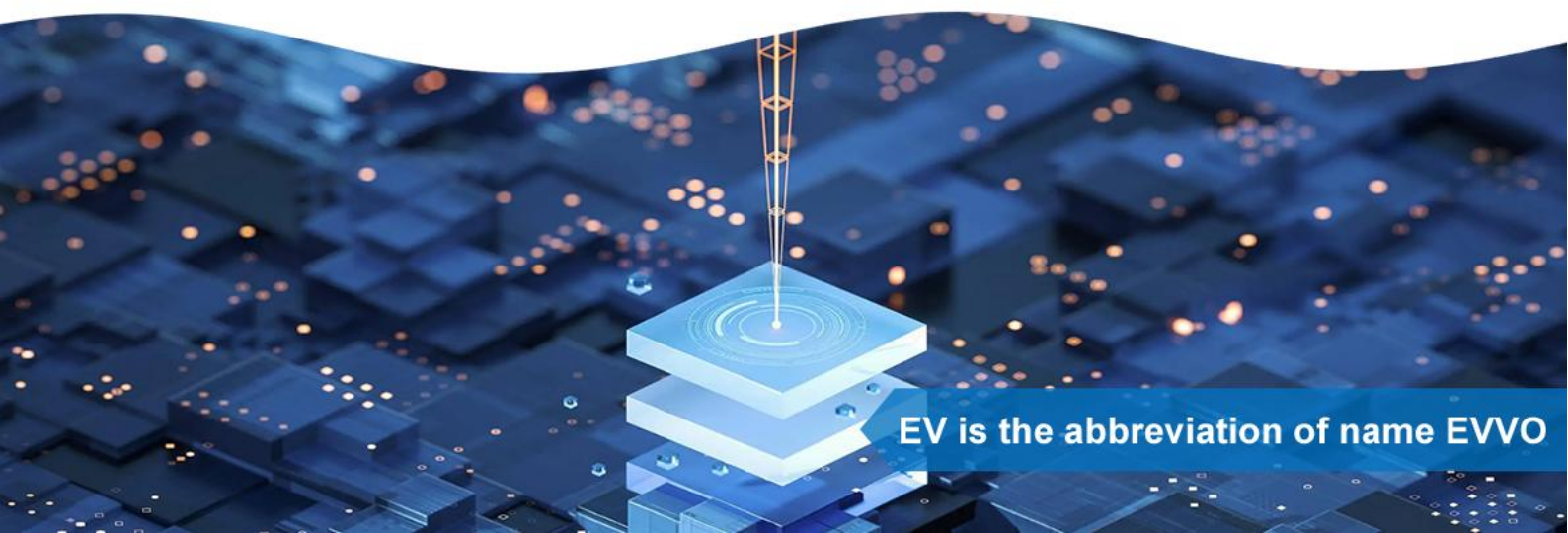
EVVOSEMI®
THINK CHANGE DO

ESD TVS MOS LDO Diode Sensor DC-DC

# Product Specification

| | |
|---|---|
| Domestic Part Number | IRF7319 |
| Overseas Part Number | IRF7319 |
| Equivalent Part Number | IRF7319 |



**Dual N + P Channel MOSFET**

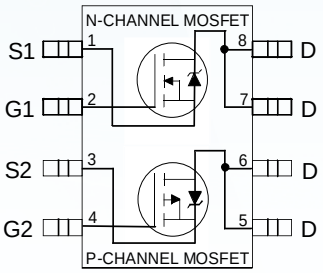
## Features

N-Ch:

- $V_{DS\ (V)}$ = 30V
- $R_{DS(ON)}$ < 31mΩ ($V_{GS}$ = 10V)
- $R_{DS(ON)}$ < 48mΩ ($V_{GS}$ = 4.5V)

P-Ch:

- $V_{DS\ (V)}$ = -30V
- $R_{DS(ON)}$ < 60mΩ ($V_{GS}$ =-10V)
- $R_{DS(ON)}$ < 100mΩ ($V_{GS}$ = -4.5V)
- Generation V Technology
- Ultra Low On-Resistance
- Dual N and P Channel MOSFET
- Surface Mount
- Fully Avalanche Rated
- Lead-Free



Top View

## Description

The SOP-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements. multiple devices can be used in an application with dramatically reducea board space. The package is designed for vapor phase, infra red, or wave soldering technigues.

## Absolute Maximum Ratings ( $T_A$ = 25°C Unless Otherwise Noted)

| | | Symbol | Maximum | | Units |
|---|---|---|---|---|---|
| | | | N-Channel | P-Channel | |
| Drain-Source Voltage | | $V_{DS}$ | 30 | -30 | V |
| Gate-Source Voltage | | $V_{GS}$ | ± 20 | | |
| Continuous Drain Current⑤ | $T_A$ = 25°C | $I_D$ | 6.5 | -4.9 | A |
| | $T_A$ = 70°C | | 5.2 | -3.9 | |
| Pulsed Drain Current | | $I_{DM}$ | 30 | -30 | |
| Continuous Source Current (Diode Conduction) | | $I_S$ | 2.5 | -2.5 | |
| Maximum Power Dissipation ⑤ | $T_A$ = 25°C | $P_D$ | 2.0 | | W |
| | $T_A$ = 70°C | | 1.3 | | |
| Single Pulse Avalanche Energy | | $E_{AS}$ | 82 | 140 | mJ |
| Avalanche Current | | $I_{AR}$ | 4.0 | -2.8 | A |
| Repetitive Avalanche Energy | | $E_{AR}$ | 0.20 | | mJ |
| Peak Diode Recovery dv/dt ② | | dv/dt | 5.0 | -5.0 | V/ ns |
| Junction and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to + 150 °C | | |

## Thermal Resistance Ratings

| Parameter | Symbol | Limit | Units |
|---|---|---|---|
| Maximum Junction-to-Ambient ⑤ | $R_{\theta JA}$ | 62.5 | °C/W |

**Dual N + P Channel MOSFET**

## Electrical Characteristics @ $T_J$ = 25°C (unless otherwise specified)

| | Parameter | | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|---|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | N-Ch | 30 | | | V | $V_{GS}$ = 0V, $I_D$ = 250μA |
| | | P-Ch | -30 | | | | $V_{GS}$ = 0V, $I_D$ = -250μA |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | N-Ch | | 0.022 | | V/°C | Reference to 25°C, $I_D$ = 1mA |
| | | P-Ch | | 0.022 | | | Reference to 25°C, $I_D$ = -1mA |
| $R_{DS(ON)}$ | Static Drain-to-Source On-Resistance | N-Ch | | 23 | 31 | mΩ | $V_{GS}$ = 10V, $I_D$ = 5.8A ④ |
| | | | | 32 | 48 | | $V_{GS}$ = 4.5V, $I_D$ = 4.7A ④ |
| | | P-Ch | | 42 | 60 | | $V_{GS}$ = -10V, $I_D$ = -4.9A ④ |
| | | | | 76 | 100 | | $V_{GS}$ = -4.5V, $I_D$ = -3.6A ④ |
| $V_{GS(th)}$ | Gate Threshold Voltage | N-Ch | 1.0 | | | V | $V_{DS}$ = $V_{GS}$, $I_D$ = 250μA |
| | | P-Ch | -1.0 | | | | $V_{DS}$ = $V_{GS}$, $I_D$ = -250μA |
| $g_{fs}$ | Forward Transconductance | N-Ch | | 14 | | S | $V_{DS}$ = 15V, $I_D$ = 5.8A ④ |
| | | P-Ch | | 7.7 | | | $V_{DS}$ = -15V, $I_D$ = -4.9A ④ |
| $I_{DSS}$ | Drain-to-Source Leakage Current | N-Ch | | | 1.0 | μA | $V_{DS}$ = 24V, $V_{GS}$ = 0V |
| | | P-Ch | | | -1.0 | | $V_{DS}$ = -24V, $V_{GS}$ = 0V |
| | | N-Ch | | | 25 | | $V_{DS}$ = 24V, $V_{GS}$ = 0V, $T_J$ = 55°C |
| | | P-Ch | | | -25 | | $V_{DS}$ = -24V, $V_{GS}$ = 0V, $T_J$ = 55°C |
| $I_{GSS}$ | Gate-to-Source Forward Leakage | N-P | | | ±100 | nA | $V_{DS}$ = ±20V |
| $Q_g$ | Total Gate Charge | N-Ch | | 22 | 33 | | N-Channel<br>$I_D$ = 5.8A, $V_{DS}$ = 15V, $V_{GS}$ = 10V ④<br>P-Channel<br>$I_D$ = -4.9A, $V_{DS}$ = -15V, $V_{GS}$ = -10V |
| | | P-Ch | | 23 | 34 | | |
| $Q_{gs}$ | Gate-to-Source Charge | | | | | | |
| $Q_{gd}$ | Gate-to-Drain ("Miller") Charge | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | N-Ch | | 8.1 | 12 | ns | N-Channel<br>$V_{DD}$ = 15V, $I_D$ = 1.0A, $R_G$ = 6.0Ω, $R_D$ = 15Ω ④<br>P-Channel<br>$V_{DD}$ = -15V, $I_D$ = -1.0A, $R_G$ = 6.0Ω, $R_D$ = 15Ω |
| | | P-Ch | | 13 | 19 | | |
| $t_r$ | Rise Time | N-Ch | | 8.9 | 13 | | |
| | | P-Ch | | 13 | 20 | | |
| $t_{d(off)}$ | Turn-Off Delay Time | N-Ch | | 26 | 39 | | |
| | | P-Ch | | 34 | 51 | | |
| $t_f$ | Fall Time | N-Ch | | 17 | 26 | | |
| | | P-Ch | | 32 | 48 | | |
| $C_{iss}$ | Input Capacitance | N-Ch | | 650 | | pF | N-Channel<br>$V_{GS}$ = 0V, $V_{DS}$ = 25V, $f$ = 1.0MHz<br>P-Channel<br>$V_{GS}$ = 0V, $V_{DS}$ = -25V, $f$ = 1.0MHz |
| | | P-Ch | | 710 | | | |
| $C_{oss}$ | Output Capacitance | N-Ch | | 320 | | | |
| | | P-Ch | | 380 | | | |
| $C_{rss}$ | Reverse Transfer Capacitance | N-Ch | | 130 | | | |
| | | P-Ch | | 180 | | | |

## Source-Drain Ratings and Characteristics

| | Parameter | | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|---|
| $I_S$ | Continuous Source Current (Body Diode) | N-Ch | | | 2.5 | A | |
| | | P-Ch | | | -2.5 | | |
| $I_{SM}$ | Pulsed Source Current (Body Diode) ① | N-Ch | | | 30 | | |
| | | P-Ch | | | -30 | | |
| $V_{SD}$ | Diode Forward Voltage | N-Ch | | 0.78 | 1.0 | V | $T_J$ = 25°C, $I_S$ = 1.7A, $V_{GS}$ = 0V ③ |
| | | P-Ch | | -0.78 | -1.0 | | $T_J$ = 25°C, $I_S$ = -1.7A, $V_{GS}$ = 0V ③ |
| $t_{rr}$ | Reverse Recovery Time | N-Ch | | 45 | 68 | ns | N-Channel<br>$T_J$ = 25°C, $I_F$ =1.7A, di/dt = 100A/μs<br>P-Channel ④<br>$T_J$ = 25°C, $I_F$ = -1.7A, di/dt = 100A/μs |
| | | P-Ch | | 44 | 66 | | |
| $Q_{rr}$ | Reverse Recovery Charge | N-Ch | | 58 | 87 | nC | |
| | | P-Ch | | 42 | 63 | | |

**Notes:**

① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 22 )

② N-Channel $I_{SD}$ ≤ 4.0A, di/dt ≤ 74A/μs, $V_{DD}$ ≤ $V_{(BR)DSS}$, $T_J$ ≤ 150°C
P-Channel $I_{SD}$ ≤ -2.8A, di/dt ≤ 150A/μs, $V_{DD}$ ≤ $V_{(BR)DSS}$, $T_J$ ≤ 150°C

③ N-Channel Starting $T_J$ = 25°C, L = 10mH $R_G$ = 25Ω, $I_{AS}$ = 4.0A. (See Figure 12)
P-Channel Starting $T_J$ = 25°C, L = 35mH $R_G$ = 25Ω, $I_{AS}$ = -2.8A.

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ Surface mounted on FR-4 board, t ≤ 10sec.

N-Channel

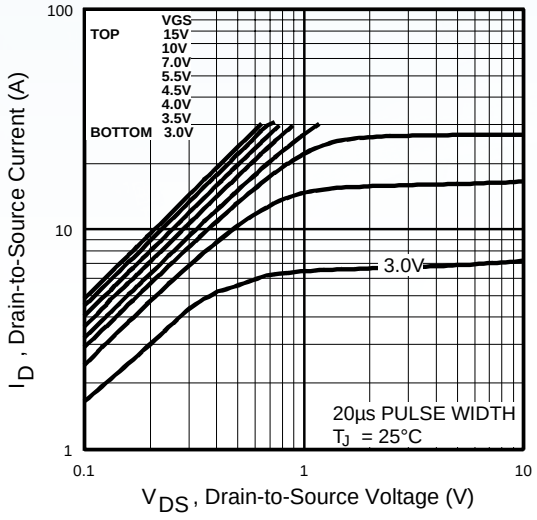



**Fig 1.** Typical Output Characteristics

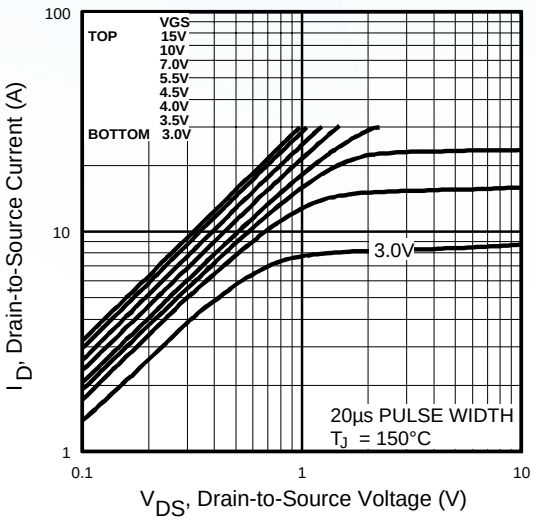



**Fig 2.** Typical Output Characteristics

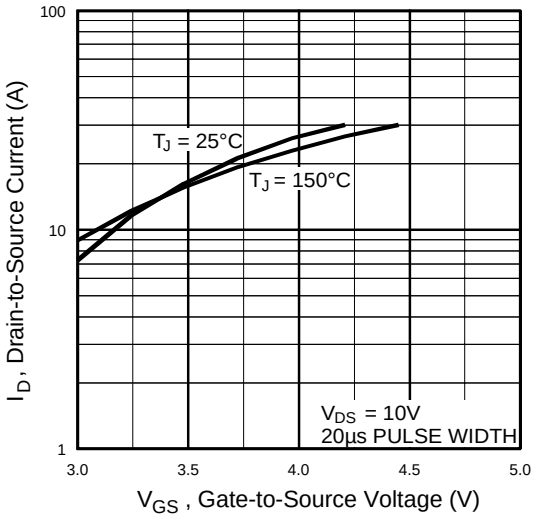



**Fig 3.** Typical Transfer Characteristics

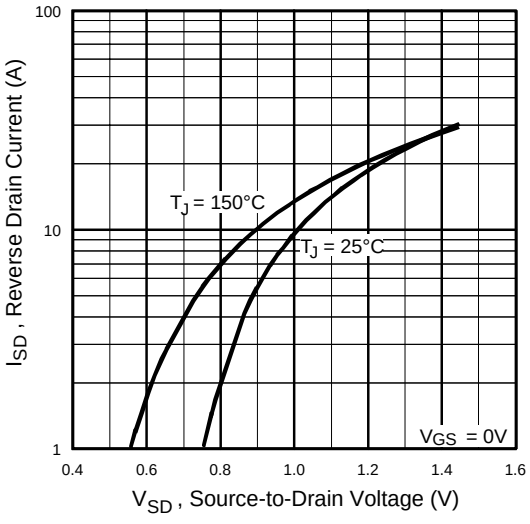



**Fig 4.** Typical Source-Drain Diode Forward Voltage

N-Channel

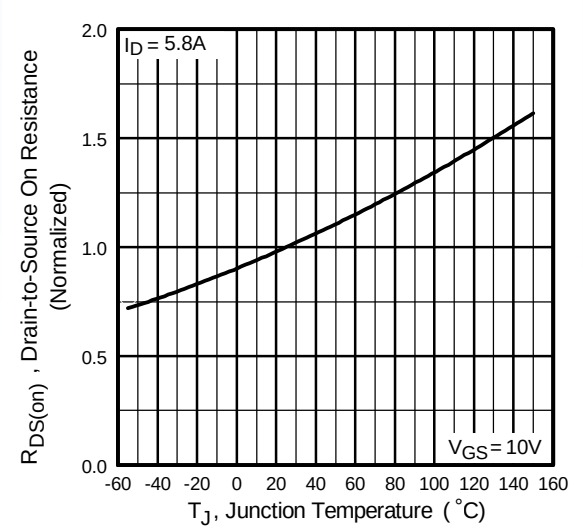



**Fig 5.** Normalized On-Resistance Vs. Temperature

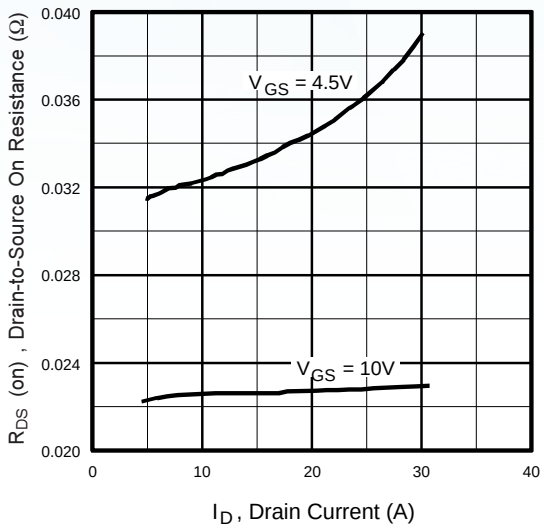



**Fig 6.** Typical On-Resistance Vs. Drain Current

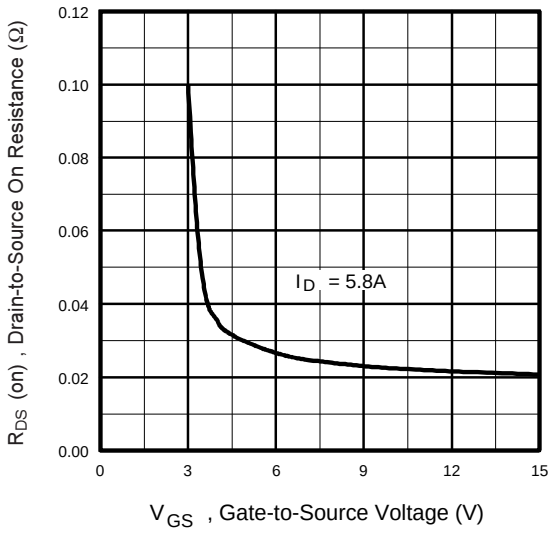



**Fig 7.** Typical On-Resistance Vs. Gate Voltage

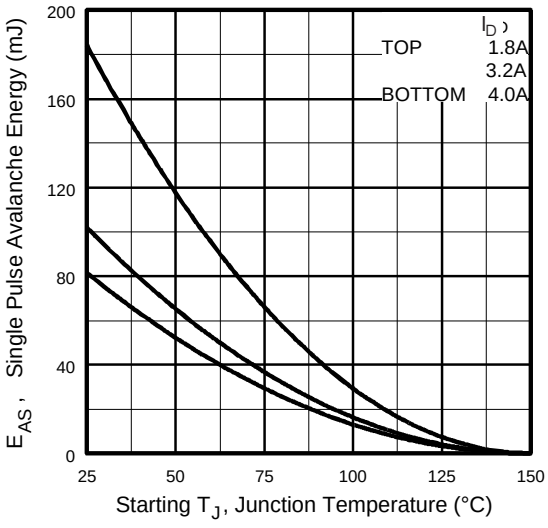



**Fig 8.** Maximum Avalanche Energy Vs. Drain Current

N-Channel

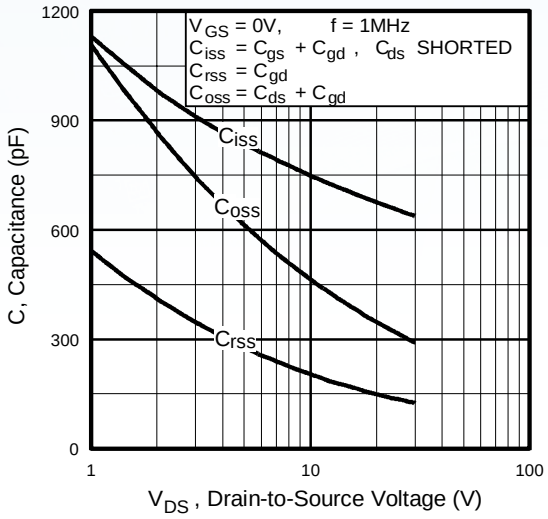



**Fig 9.** Typical Capacitance Vs. Drain-to-Source Voltage

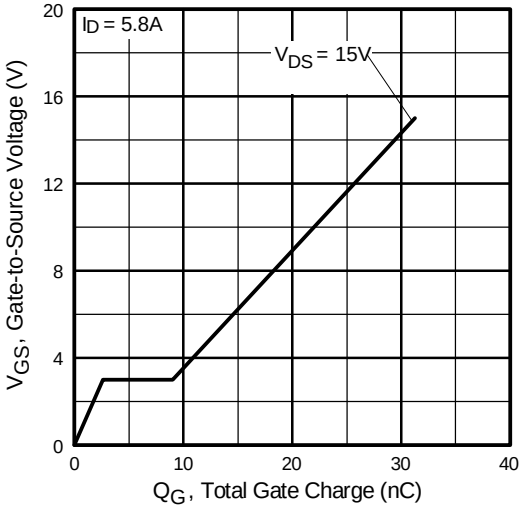



**Fig 10.** Typical Gate Charge Vs. Gate-to-Source Voltage

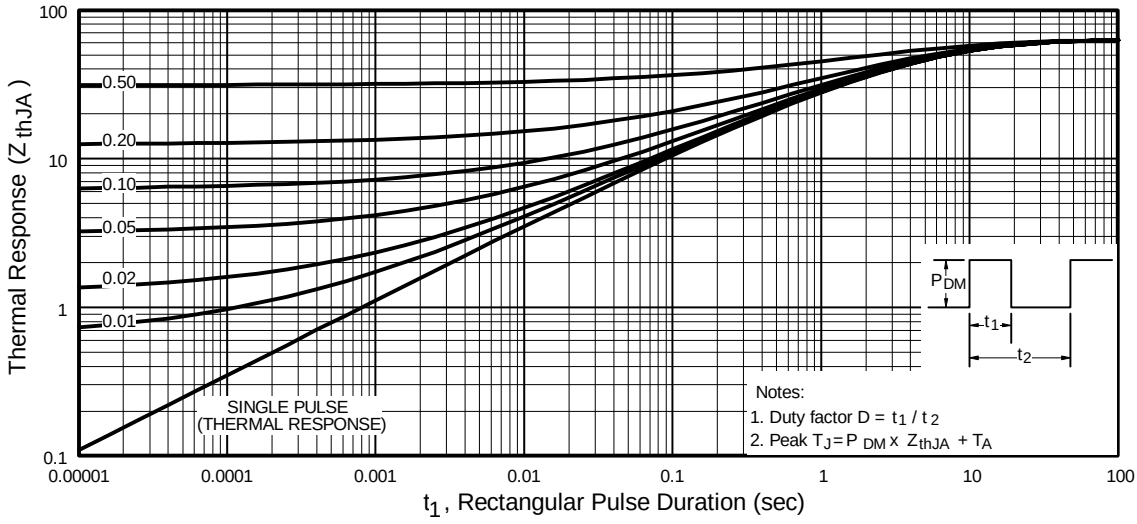



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

## P-Channel

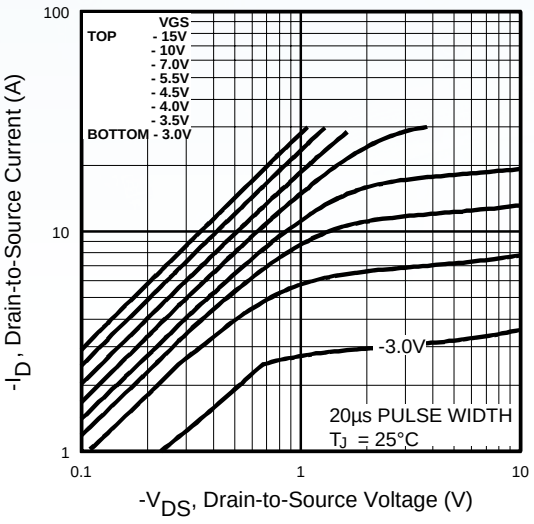



**Fig 12.** Typical Output Characteristics

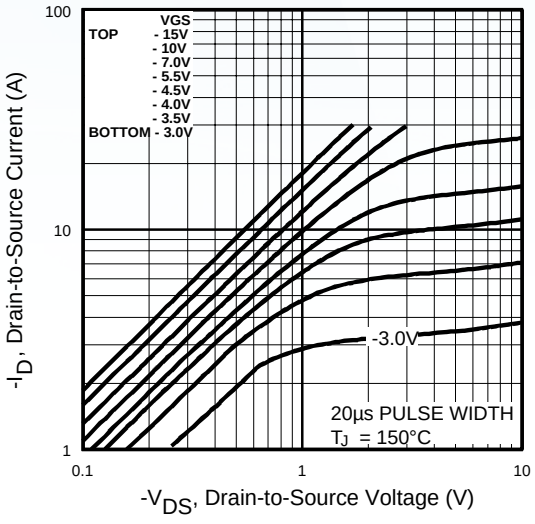



**Fig 13.** Typical Output Characteristics

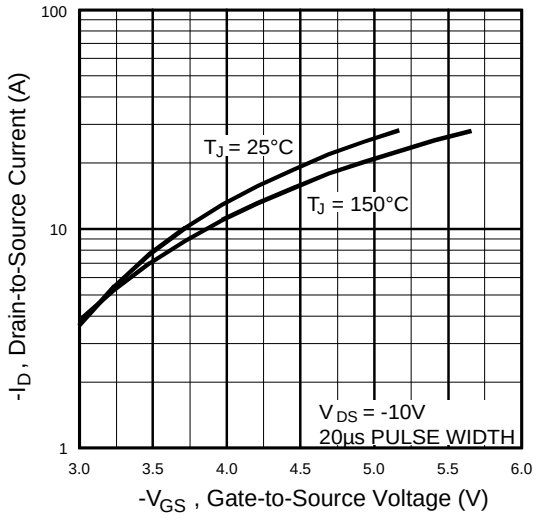



**Fig 14.** Typical Transfer Characteristics

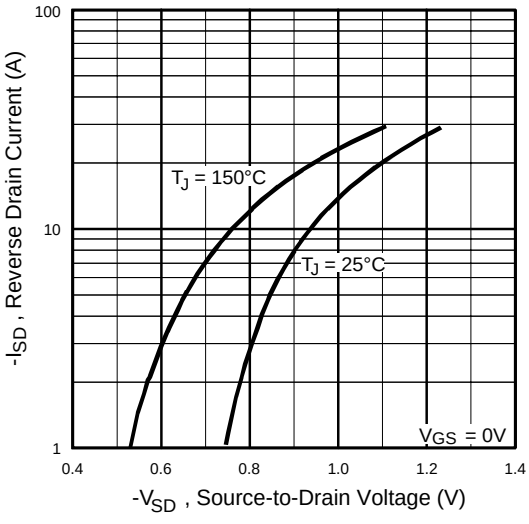



**Fig 15.** Typical Source-Drain Diode Forward Voltage

## P-Channel

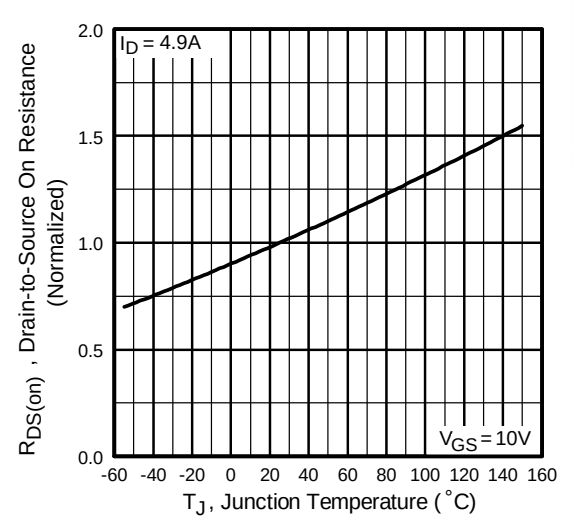



**Fig 16.** Normalized On-Resistance Vs. Temperature

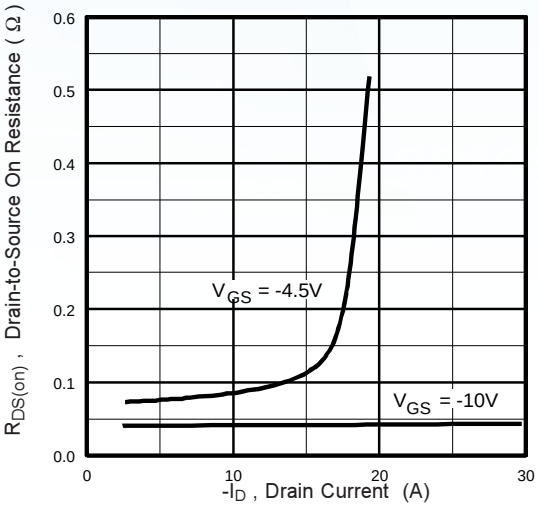



**Fig 17.** Typical On-Resistance Vs. Drain Current

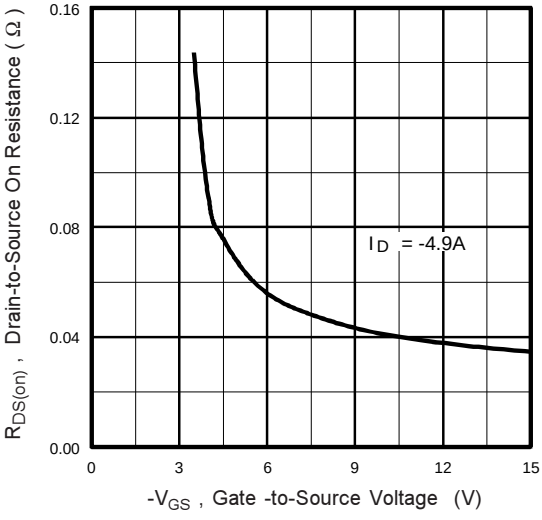



**Fig 18.** Typical On-Resistance Vs. Gate Voltage

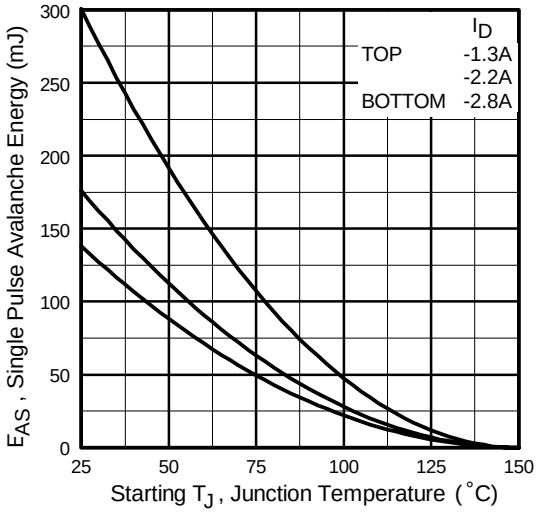



**Fig 19.** Maximum Avalanche Energy Vs. Drain Current

P-Channel

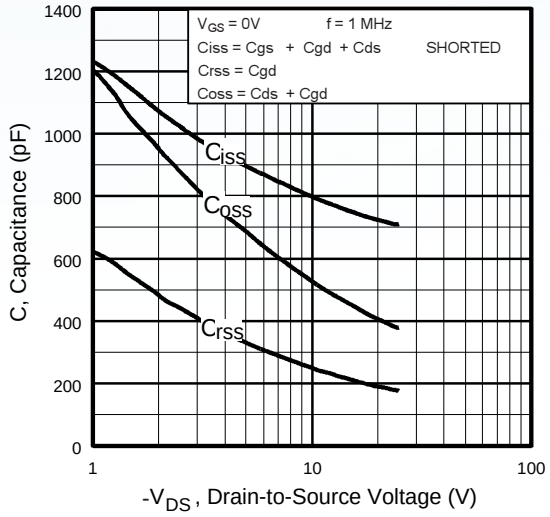



**Fig 20.** Typical Capacitance Vs. Drain-to-Source Voltage

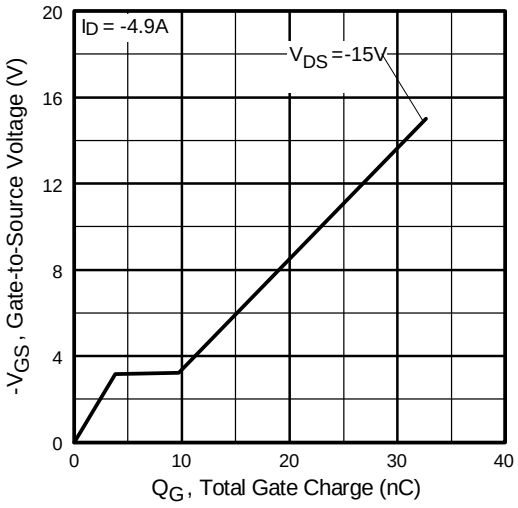



**Fig 21.** Typical Gate Charge Vs. Gate-to-Source Voltage

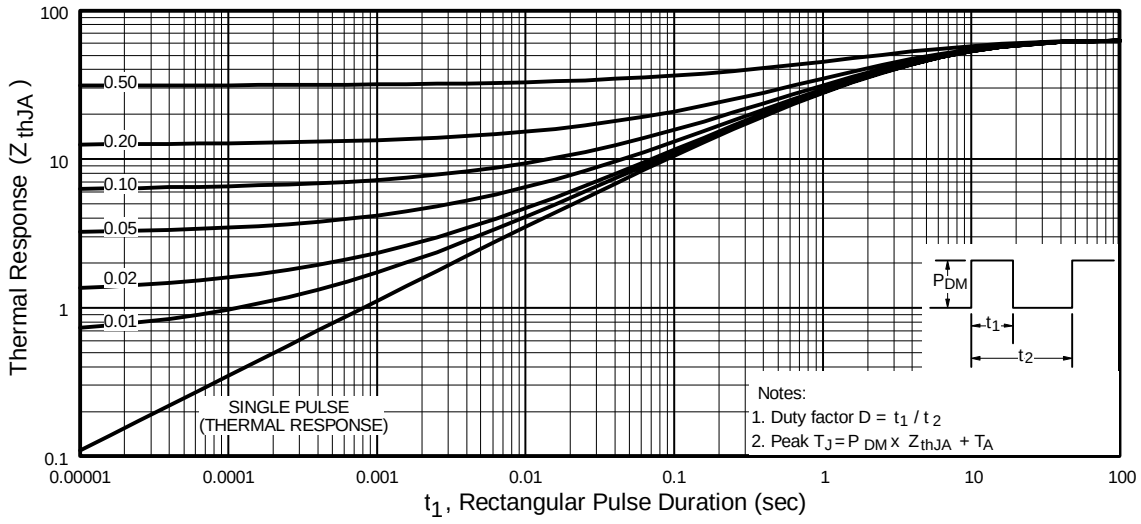
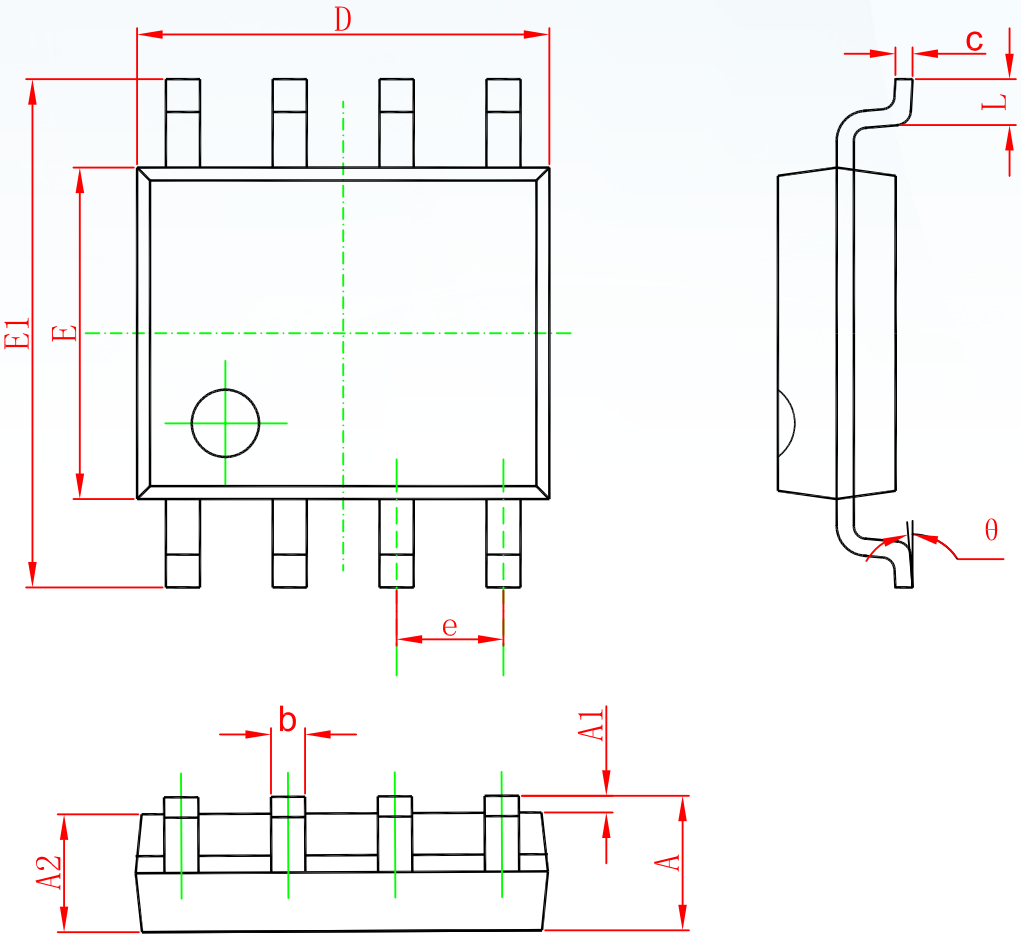



**Fig 22.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Dual N + P Channel MOSFET

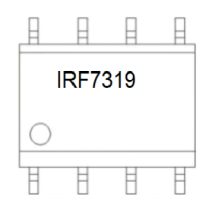
**SOP-8**




| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|---|---|---|---|---|
| | Min | Max | Min | Max |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.006 | 0.010 |
| D | 4.700 | 5.100 | 0.185 | 0.200 |
| E | 3.800 | 4.000 | 0.150 | 0.157 |
| E1 | 5.800 | 6.200 | 0.228 | 0.244 |
| e | 1.270(BSC) | | 0.050(BSC) | |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |

**Dual N + P Channel MOSFET**

## Marking




## Ordering information

| Order code | Package | Baseqty | Deliverymode |
|---|---|---|---|
| IRF7319 | SOP-8 | 3000 | Tape and reel |

# Disclaimer

EVVOSEMI ("EVVO") reserves the right to make corrections, enhancements, improvements, and other changes to its products and services at any time, and to discontinue any product or service without notice.

EVVO warrants the performance of its hardware products to the specifications applicable at the time of sale in accordance with its standard warranty. Testing and other quality control techniques are used as deemed necessary by EVVO to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

Customers should obtain and confirm the latest product information and specifications before final design, purchase, or use. EVVO makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does EVVO assume any liability for application assistance or customer product design. EVVO does not warrant or accept any liability for products that are purchased or used for any unintended or unauthorized application.

EVVO products are not authorized for use as critical components in life support devices or systems without the express written approval of EVVOSEMI.

The EVVO logo and EVVOSEMI are trademarks of EVVOSEMI or its subsidiaries in relevant jurisdictions. EVVO reserves the right to make changes without further notice to any products herein.